

**Silicon NPN Power Transistors**

**2SC3795B**

**DESCRIPTION**

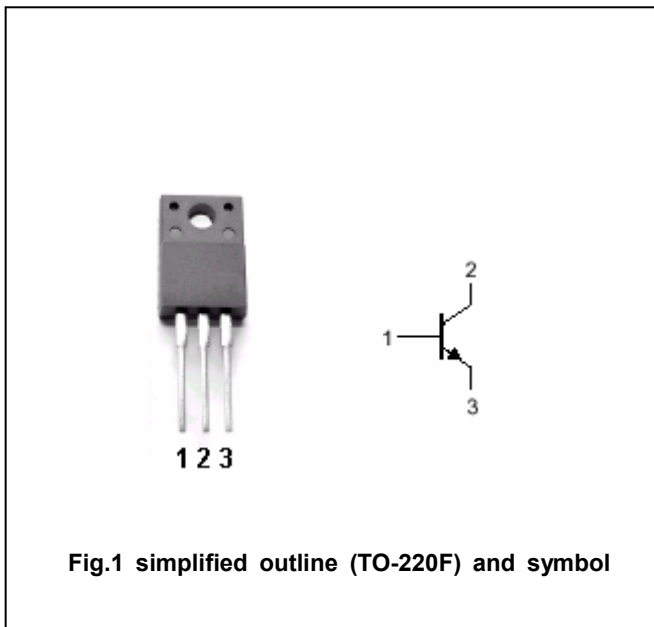
- With TO-220F package
- High breakdown voltage
- Fast switching speed
- Low collector saturation voltage

**APPLICATIONS**

- For high voltage ,high-speed switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1300	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	600	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	8	V
I <sub>C</sub>	Collector current		6	A
I <sub>B</sub>	Base current		3	A
P <sub>C</sub>	Collector dissipation	T <sub>a</sub> =25°C	2	W
		T <sub>C</sub> =25°C	50	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.2A , L=25mH	600			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.6A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.6A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =800V; I <sub>E</sub> =0			100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			100	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V	15			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =5V	8			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V		8		MHz

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PACKAGE OUTLINE

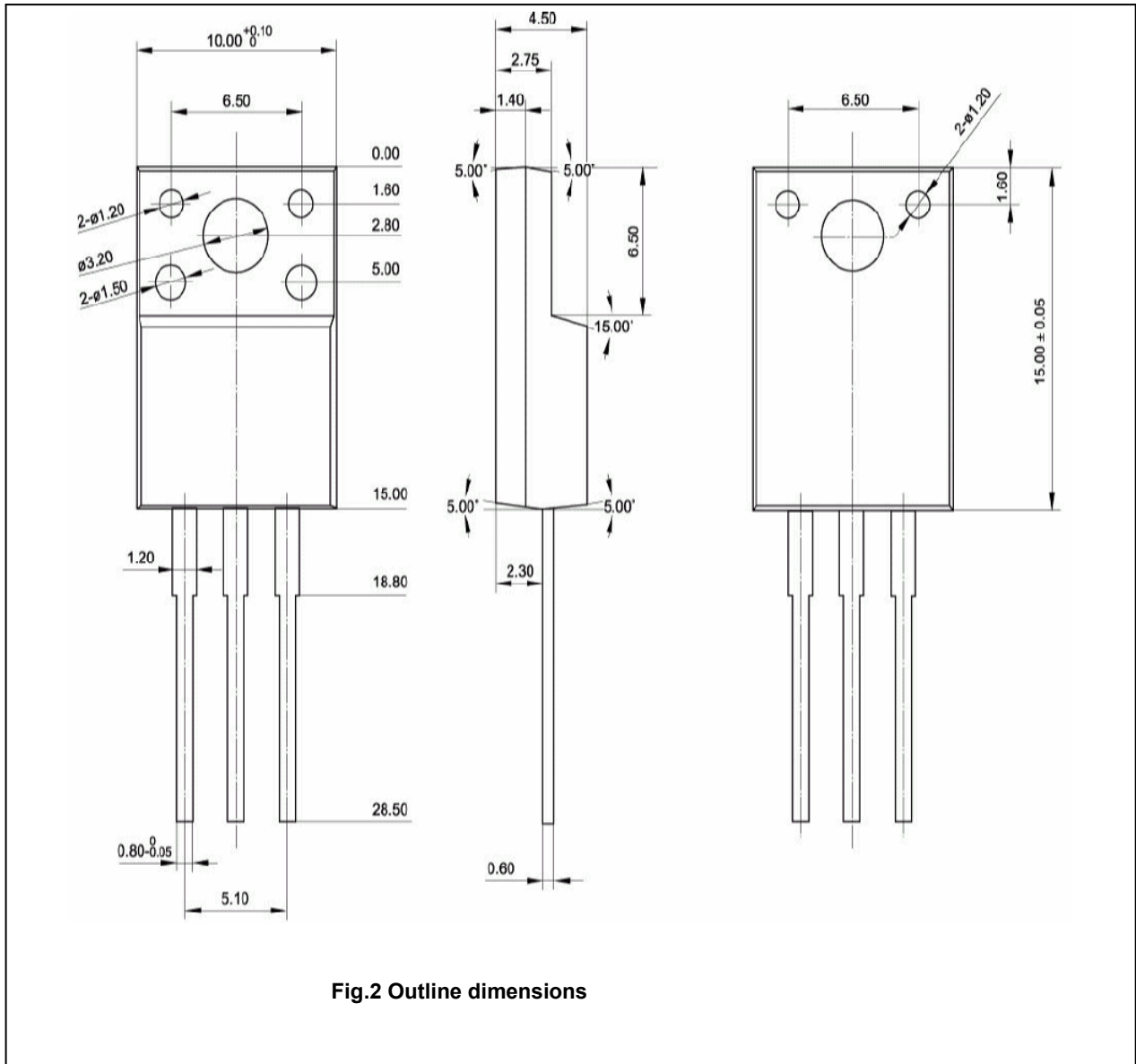


Fig.2 Outline dimensions